

## **Vishay Semiconductors**

| ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>  |   |                                      |                        |                  |  |  |  |
|--|---|--------------------------------------|------------------------|------------------|--|--|--|
| PARAMETER  | TEST CONDITION                          | SYMBOL                               | VALUE                  | UNIT             |  |  |  |
| OUTPUT   | · · ·                                   |                                      |                        |                  |  |  |  |
| High peak output current <sup>(2)</sup>  |   | I <sub>OH(PEAK)</sub>                | 0.6                    | А                |  |  |  |
| Low peak output current (2)  |   | I <sub>OL(PEAK)</sub>                | 0.6                    | А                |  |  |  |
| Supply voltage   |   | (V <sub>CC</sub> - V <sub>EE</sub> ) | 0 to + 35              | V                |  |  |  |
| Output voltage   |   | V <sub>O(PEAK)</sub>                 | 0 to + V <sub>CC</sub> | V                |  |  |  |
| Output power dissipation   |   | P <sub>diss</sub>                    | 250                    | mW               |  |  |  |
| OPTOCOUPLER  | · · ·                                   |                                      | · · ·                  |                  |  |  |  |
| Isolation test voltage<br>between emitter and detector, climate<br>per DIN 500414, part 2, Nov. 74 | t = 1.0 min                             | V <sub>ISO</sub>                     | 5300                   | V <sub>RMS</sub> |  |  |  |
| Storage temperature range  |   | Τ <sub>S</sub>                       | - 55 to + 125          | ۵°               |  |  |  |
| Ambient operating temperature range  |   | T <sub>A</sub>                       | - 40 to + 110          | °C               |  |  |  |
| Total power dissipation  |   | P <sub>tot</sub>                     | 285                    | mW               |  |  |  |
| Lead solder temperature (3)  | for 10 s,<br>1.6 mm below seating plane |                                      | 260                    | °C               |  |  |  |

#### Notes

<sup>(1)</sup>  $T_{amb} = 25$  °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

<sup>(2)</sup> Maximum pulse width = 10  $\mu$ s, maximum duty cycle = 0.2 %. This value is intended to allow for component tolerances for designs with  $I_O$  peak minimum = 2.5 A. See applications section for additional details on limiting  $I_{OH}$  peak.

(3) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

| RECOMMENDED OPERATING CONDITION |                                   |      |       |      |  |  |  |
|---------------------------------|-----------------------------------|------|-------|------|--|--|--|
| PARAMETER                       | SYMBOL                            | MIN. | MAX.  | UNIT |  |  |  |
| Power supply voltage            | V <sub>CC</sub> - V <sub>EE</sub> | 15   | 30    | V    |  |  |  |
| Input LED current (ON)          | I <sub>F</sub>                    | 7    | 16    | mA   |  |  |  |
| Input voltage (OFF)             | V <sub>F(OFF)</sub>               | - 3  | 0.8   | V    |  |  |  |
| Operating temperature           | T <sub>amb</sub>                  | - 40 | + 110 | ٥°C  |  |  |  |

| THERMAL CHARACTERISTICS                                   |                |                   |       |      |
|---|----------------|-------------------|-------|------|
| PARAMETER   | TEST CONDITION | SYMBOL            | VALUE | UNIT |
| LED power dissipation                                     | at 25 °C       | P <sub>diss</sub> | 35    | mW   |
| Output power dissipation                                  | at 25 °C       | P <sub>diss</sub> | 250   | mW   |
| Total power dissipation                                   | at 25 °C       | P <sub>tot</sub>  | 285   | mW   |
| Maximum LED junction temperature                          | at 25 °C       | T <sub>jmax</sub> | 125   | °C   |
| Maximum output die junction temperature                   | at 25 °C       | T <sub>jmax</sub> | 125   | °C   |
| Thermal resistance, junction emitter to board             | at 25 °C       | $\theta_{JEB}$    | 169   | °C/W |
| Thermal resistance, junction emitter to case              | at 25 °C       | $\theta_{JEC}$    | 192   | °C/W |
| Thermal resistance, junction detector to board            | at 25 °C       | $\theta_{JDB}$    | 82    | °C/W |
| Thermal resistance, junction detector to case             | at 25 °C       | θJDC              | 80    | °C/W |
| Thermal resistance, junction emitter to junction detector | at 25 °C       | $\theta_{JED}$    | 200   | °C/W |
| Thermal resistance, case to ambient                       | at 25 °C       | $\theta_{CA}$     | 2645  | °C/W |

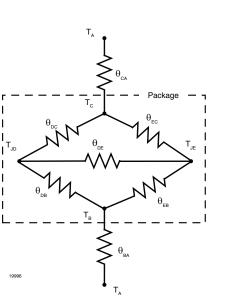
#### Note

The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's thermal characteristics of optocouplers application note.

Document Number: 83875 Rev. 1.9, 15-Apr-08

# Vishay Semiconductors





| ELECTRICAL CHARACTERISTICS <sup>(1)</sup>  |  |                                |                       |                       |      |       |  |
|--|--|--------------------------------|-----------------------|-----------------------|------|-------|--|
| PARAMETER                                  | TEST CONDITION   | SYMBOL                         | MIN.                  | TYP.                  | MAX. | UNIT  |  |
| High lovel output ourrept                  | $R_g = 2.3 \Omega, C_g = 22 nF$                          | I <sub>OH</sub> <sup>(2)</sup> | 0.1                   | 0.4                   |      | А     |  |
| High level output current                  | $R_g = 2.3 \Omega, C_g = 22 nF$                          | I <sub>OH</sub> <sup>(3)</sup> | 0.5                   |                       |      | A     |  |
| Low lovel output ourrent                   | $R_g = 2.3 \Omega, C_g = 22 nF$                          | I <sub>OL</sub> <sup>(2)</sup> | 0.1                   | 0.6                   |      | А     |  |
| Low level output current                   | $R_g = 2.3 \Omega, C_g = 22 nF$                          | I <sub>OL</sub> <sup>(3)</sup> | 0.5                   |                       |      | А     |  |
| High level output voltage                  | I <sub>O</sub> = - 100 mA                                | V <sub>OH</sub> <sup>(4)</sup> | V <sub>CC</sub> - 1.5 | V <sub>CC</sub> - 0.6 |      | V     |  |
| Low level output voltage                   | I <sub>O</sub> = 100 mA                                  | V <sub>OL</sub>                |                       | 0.3                   | 1.0  | V     |  |
| High level supply current                  | Output open, I <sub>F</sub> = 8 to 16 mA                 | I <sub>CCH</sub>               |                       | 4.2                   | 7.0  | mA    |  |
| Low level supply current                   | Output open,<br>$V_F = -3.0 \text{ to } + 0.8 \text{ V}$ | I <sub>CCL</sub>               |                       | 3.7                   | 7.0  | mA    |  |
| Threshold input current low to high        | $I_{O} = 0 \text{ mA}, V_{O} > 5 \text{ V}$              | I <sub>FLH</sub>               |                       | 1.1                   | 5.0  | mA    |  |
| Threshold input voltage high to low        |  | V <sub>FHL</sub>               | 0.8                   |                       |      | V     |  |
| Input forward voltage                      | I <sub>F</sub> = 10 mA                                   | V <sub>F</sub>                 | 1.0                   | 1.3                   | 1.6  | V     |  |
| Temperature coefficient of forward voltage | I <sub>F</sub> = 10 mA                                   | $\Delta V_{F} / \Delta T_{A}$  |                       | - 1.4                 |      | mV/°C |  |
| Input reverse breakdown voltage            | I <sub>R</sub> = 10 μA                                   | BV <sub>R</sub>                | 5                     |                       |      | V     |  |
| Input capacitance                          | $f = 1 MHz, V_F = 0 V$                                   | C <sub>IN</sub>                |                       | 60                    |      | pF    |  |
| IN/I O threaded                            | $V_O \ge 5 V$  | V <sub>UVLO+</sub>             | 11.0                  | 12.2                  | 13.5 | V     |  |
| UVLO threshold                             | I <sub>F</sub> = 10 mA                                   | V <sub>UVLO-</sub>             | 9.5                   | 10.7                  | 12.0 | V     |  |
| UVLO hysteresis                            |  | UVLO <sub>HYS</sub>            |                       | 1.5                   |      | V     |  |

#### Notes

<sup>(1)</sup> Minimum and maximum values were tested over recommended operating conditions ( $T_A = -40$  °C to 110 °C,  $I_{F(ON)} = 7$  mA to 16 mA,  $V_{F(OFF)} = -3.0$  V to 0.8 V,  $V_{CC} = 15$  V to 30 V,  $V_{EE} =$  ground) unless otherwise specified. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements. All typical values were measured at  $T_{amb} = 25$  °C and with  $V_{CC} - V_{EE} = 30$  V.

<sup>(2)</sup> Maximum pulse width = 50  $\mu$ s, maximum duty cycle = 0.5 %.

(3) Maximum pulse width = 10  $\mu$ s, maximum duty cycle = 0.2 %. This value is intended to allow for component tolerances for designs with  $I_O$  peak minimum = 0.5 A.

(4) In this test V<sub>OH</sub> is measured with a dc load current. When driving capacitive loads V<sub>OH</sub> will approach V<sub>CC</sub> as I<sub>OH</sub> approaches zero amps. Maximum pulse width = 1 ms, maximum duty cycle = 20 %.



Vishay Semiconductors

### **TEST CIRCUITS**

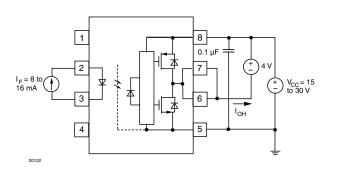


Fig. 1 - I<sub>OH</sub> Test Circuit

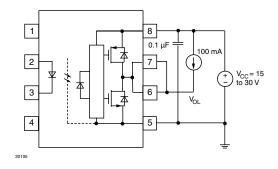


Fig. 4 - V<sub>OL</sub> Test Circuit

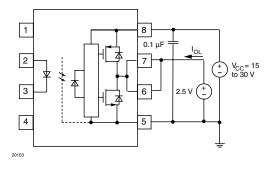
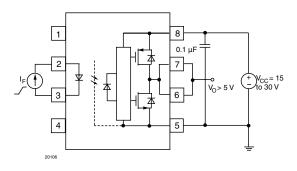


Fig. 2 - I<sub>OL</sub> Test Circuit





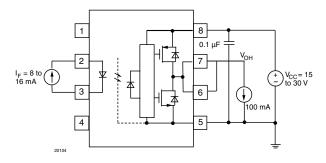


Fig. 3 - V<sub>OH</sub> Test Circuit

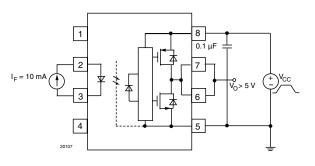


Fig. 6 - UVLO Test Circuit

Document Number: 83875 Rev. 1.9, 15-Apr-08

# Vishay Semiconductors

## Optocoupler, IGBT and MOSFET Driver



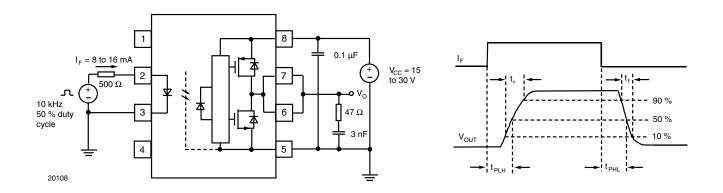
| SWITCHING CHARACTERISTICS <sup>(1)</sup>                          |   |  |        |      |      |      |  |
|---|---|--|--------|------|------|------|--|
| PARAMETER   | TEST CONDITION  | SYMBOL                                     | MIN.   | TYP. | MAX. | UNIT |  |
| Propagation delay time to logic low output <sup>(1)</sup>         | $\label{eq:Rg} \begin{array}{l} R_{g} = 47\;\Omega,C_{g} = 3\;nF,f = 10\;kHz,\\ duty\;cycle = 50\;\% \end{array}$   | t <sub>PHL</sub>                           | 0.2    |      | 0.4  | μs   |  |
| Propagation delay time to logic high output <sup>(1)</sup>        | $\label{eq:Rg} \begin{array}{l} R_{g} = 47\;\Omega,C_{g} = 3\;nF,f = 10\;kHz,\\ & duty\;cycle = 50\;\% \end{array}$ | t <sub>PLH</sub>                           | 0.2    |      | 0.4  | μs   |  |
| Pulse width distortion <sup>(2)</sup>                             | $\label{eq:Rg} \begin{array}{l} R_{g} = 47\;\Omega,C_{g} = 3\;nF,f = 10\;kHz,\\ duty\;cycle = 50\;\% \end{array}$   | PWD  |        |      | 0.2  | μs   |  |
| Propagation delay difference between any two parts <sup>(3)</sup> | $\label{eq:Rg} \begin{array}{l} R_{g} = 47\;\Omega,C_{g} = 3\;nF,f = 10\;kHz,\\ duty\;cycle = 50\;\% \end{array}$   | PDD (t <sub>PHL</sub> - t <sub>PLH</sub> ) | - 0.35 |      | 0.35 | μs   |  |
| Rise time   | $\label{eq:Rg} \begin{array}{l} R_{g} = 47\;\Omega,C_{g} = 3\;nF,f = 10\;kHz,\\ duty\;cycle = 50\;\% \end{array}$   | tr   |        | 0.1  |      | μs   |  |
| Fall time   | $\label{eq:Rg} \begin{array}{l} R_{g} = 47\;\Omega,C_{g} = 3\;nF,f = 10\;kHz,\\ duty\;cycle = 50\;\% \end{array}$   | t <sub>f</sub>                             |        | 0.01 |      | μs   |  |
| UVLO turn on delay  | $V_{O} > 5 V, I_{F} = 10 mA$  | T <sub>UVLO-ON</sub>                       |        | 1.1  |      | μs   |  |
| UVLO turn off delay   | V <sub>O</sub> > 5 V, I <sub>F</sub> = 10 mA  | T <sub>UVLO-OFF</sub>                      |        | 1.1  |      | μs   |  |

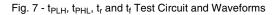
#### Notes

 $^{(1)}$  This load condition approximates the gate load of a 1200 V/25 A IGBT.

 $^{(2)}$  Pulse Width Distortion (PWD) is defined as  $|t_{\mathsf{PHL}}\text{-}t_{\mathsf{PLH}}|$  for any given device.

<sup>(3)</sup> The difference between t<sub>PHL</sub> and t<sub>PLH</sub> between any two VO3150 parts under the same test condition.





| COMMON MODE TRANSIENT IMMUNITY  |  |                 |      |      |      |       |  |
|---|--|-----------------|------|------|------|-------|--|
| PARAMETER   | TEST CONDITION   | SYMBOL          | MIN. | TYP. | MAX. | UNIT  |  |
| Common mode transient immunity at logic high output <sup>(1, 2)</sup> | $T_A = 25 \ ^{\circ}C, I_F = 10 \text{ to } 16 \text{ mA}, V_{CM} = 1500 \text{ V}, V_{CC} = 30 \text{ V}$ | CM <sub>H</sub> | 15   | 30   |      | kV/μs |  |
| Common mode transient immunity at logic low output <sup>(1, 3)</sup>  |  | CM <sub>L</sub> | 15   | 30   |      | kV/μs |  |

#### Notes

<sup>(1)</sup> Pins 1 and 4 need to be connected to LED common.

<sup>(2)</sup> Common mode transient immunity in the high state is the maximum tolerable  $|dV_{CM}/dt|$  of the common mode pulse,  $V_{CM}$ , to assure that the output will remain in the high state (i.e.,  $V_O > 15$  V).

(3) Common mode transient immunity in a low state is the maximum tolerable  $|dV_{CM}/dt|$  of the common mode pulse,  $V_{CM}$ , to assure that the output will remain in a low state (i.e.,  $V_O < 1$  V).



5\

20109

3

4

## Optocoupler, IGBT and MOSFET Driver

# Vishay Semiconductors

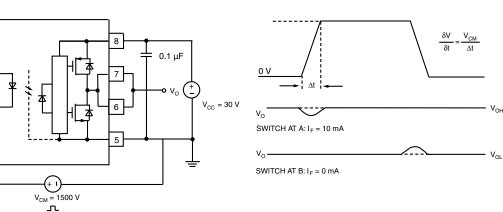
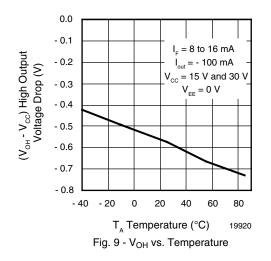


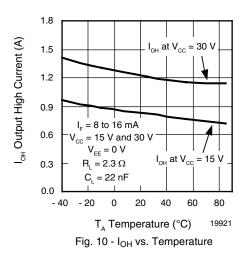
Fig. 8 - CMR Test Circuit and Waveforms

| PARAMETER  | TEST CONDITION | SYMBOL            | MIN. | TYP.      | MAX. | UNIT |
|--|----------------|-------------------|------|-----------|------|------|
| Climatic classification<br>(according to IEC68 part 1) |                |                   |      | 55/110/21 |      |      |
| Comparative tracking index                             |                | CTI               | 175  |           | 399  |      |
| Peak transient overvoltage                             |                | V <sub>IOTM</sub> | 8000 |           |      | V    |
| Peak insulation voltage                                |                | V <sub>IORM</sub> | 630  |           |      | V    |
| Safety rating - power output                           |                | P <sub>SO</sub>   |      |           | 500  | mW   |
| Safety rating - input current                          |                | I <sub>SI</sub>   |      |           | 300  | mA   |
| Safety rating - temperature                            |                | T <sub>SI</sub>   |      |           | 175  | °C   |
| Creepage distance                                      | standard DIP-8 |                   | 7    |           |      | mm   |
| Clearance distance                                     | standard DIP-8 |                   | 7    |           |      | mm   |
| Creepage distance                                      | 400 mil DIP-8  |                   | 8    |           |      | mm   |
| Clearance distance                                     | 400 mil DIP-8  |                   | 8    |           |      | mm   |

#### Note

As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of prodective circuits.





# VO3150

# Vishay Semiconductors

Optocoupler, IGBT and MOSFET Driver



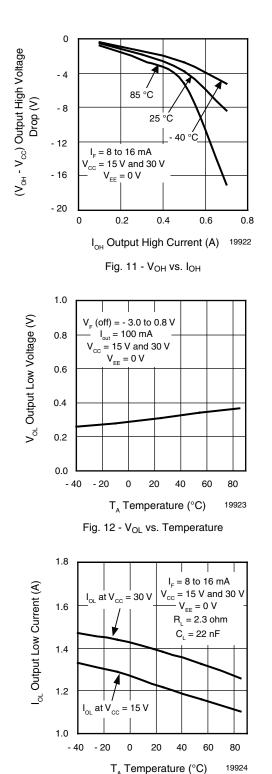


Fig. 13 - I<sub>OL</sub> vs. Temperature

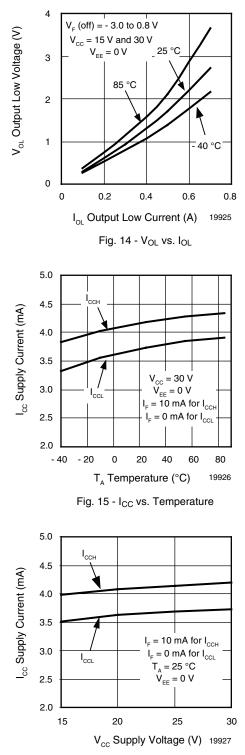


Fig. 16 - I<sub>CC</sub> vs. V<sub>CC</sub>



## **Vishay Semiconductors**

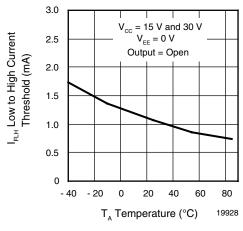


Fig. 17 - I<sub>FLH</sub> vs. Temperature

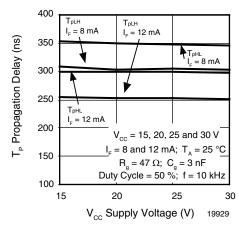
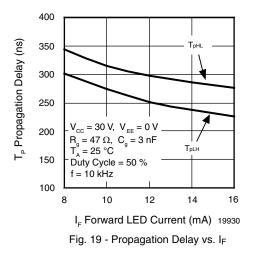


Fig. 18 - Propagation Delay vs.  $V_{CC}$ 



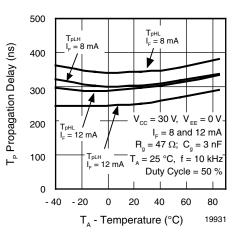
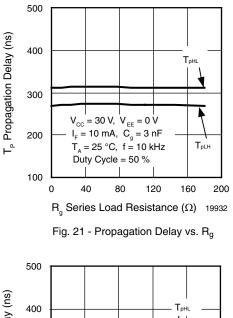


Fig. 20 - Propagation Delay vs. Temperature



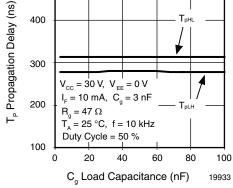


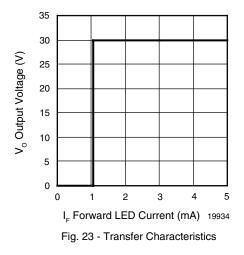
Fig. 22 - Propagation Delay vs. Cg

# VO3150

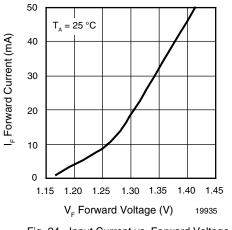
# Vishay Semiconductors

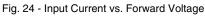
Optocoupler, IGBT and MOSFET Driver

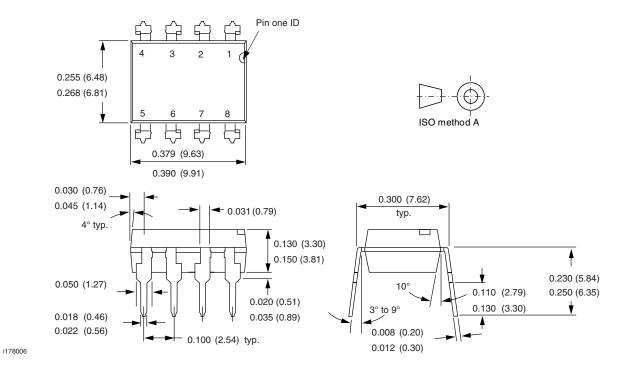














## Vishay Semiconductors

### **OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Vishay

# Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.